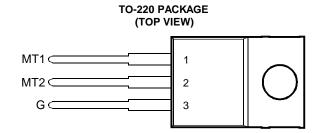


- High Current Triacs
- 16 A RMS
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- 125 A Peak Current
- Max I_{GT} of 50 mA (Quadrants 1 3)



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING			VALUE	UNIT
	TR16-400-125		400	
Repetitive peak off-state voltage (see Note 1)	TR16-600-125	\/	600	V
	TR16-700-125	V_{DRM}	700	V
	TR16-800-125		800	
Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2)			16	Α
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)			125	Α
Peak gate current			±1	Α
Operating case temperature range			-40 to +110	°C
Storage temperature range			-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds			230	°C

- NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
 - 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 400 mA/°C.
 - 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER			TEST CONDITIONS			TYP	MAX	UNIT
I _{DRM}	Repetitive peak off-state current	V_D = rated V_{DRM}	I _G = 0	T _C = 110°C			±2	mA
		V _{supply} = +12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs		12	50	mA
I _{GT}	Gate trigger	$V_{\text{supply}} = +12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-19	-50	
	current	V _{supply} = -12 V†	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-16	-50	
		V _{supply} = -12 V†	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		34		
		V _{supply} = +12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs		8.0	2	V
V _{GT}	Gate trigger	$V_{\text{supply}} = +12 \text{ V}\dagger$	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-0.8	-2	
	voltage	V _{supply} = -12 V†	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		-0.8	-2	
		V _{supply} = -12 V†	$R_L = 10 \Omega$	$t_{p(g)} > 20 \mu s$		0.9	2	
V _T	On-state voltage	I _{TM} = ±22.5 A	$I_G = 50mA$	(see Note 4)		±1.4	±1.7	V
I _H	Holding current	V _{supply} = +12 V†	$I_G = 0$	Init' I _{TM} = 100 mA		22	40	mA
		$V_{\text{supply}} = -12 \text{ V}^{\dagger}$	I _G = 0	Init' $I_{TM} = -100 \text{ mA}$		-12	-40	ША

[†] All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques, t_p = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

	PARAMETER TEST CONDITIONS		MIN	TYP	MAX	UNIT		
IL	Latching current	$V_{\text{supply}} = +12 \text{ V}^{\dagger}$ $V_{\text{supply}} = -12 \text{ V}^{\dagger}$	(see Note 5)				80 -80	mA
dv/dt	Critical rate of rise of off-state voltage	V_D = Rated V_D	I _G = 0	T _C = 110°C		±400		V/µs
dv/dt _(c)	Critical rise of commutation voltage	V_D = Rated V_D di/dt = 0.5 $I_{T(RMS)}$ /ms		$T_{C} = 80^{\circ}C$ $I_{T} = 1.4 I_{T(RMS)}$	±1.2	±9		V/µs
di/dt	Critical rate of rise of on -state current	V_D = Rated V_D di_G/dt = 50 mA/ μ s	$I_{GT} = 50 \text{ mA}$	T _C = 110°C		±100		A/µs

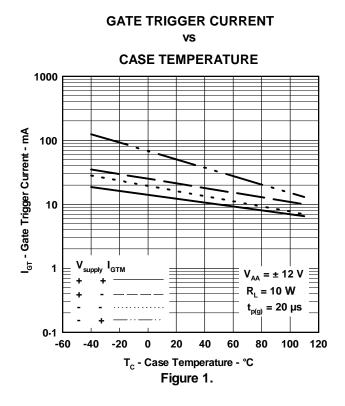
[†] All voltages are with respect to Main Terminal 1.

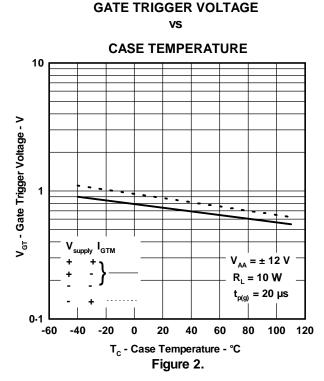
NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G = 100 \ \Omega$, $t_{p(q)} = 20 \ \mu s$, $t_r = \le 15 \ ns$, $f = 1 \ kHz$.

thermal characteristics

PARAMETER			TYP	MAX	UNIT
R _{θJC} Junction to case them	nal resistance			1.9	°C/W
R _{θJA} Junction to free air the	ermal resistance			62.5	°C/W

TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS

